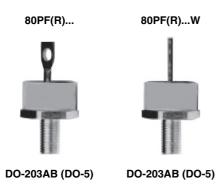


Vishay Semiconductors

Standard Recovery Diodes, Generation 2 DO-5 (Stud Version), 80 A



FEATURES





- Designed for a wide range of applications
- Stud cathode and stud anode version
- · Wire version available
- Low thermal resistance
- UL approval pending
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for multiple level

PRODUCT SUMMARY				
I _{F(AV)}	80 A			

TYPICAL APPLICATIONS

- · Battery chargers
- Converters
- · Power supplies
- · Machine tool controls
- Welding

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		80	А	
I _{F(AV)}	T _C	140	°C	
I _{F(RMS)}		126	А	
1	50 Hz	1500	٨	
I _{FSM}	60 Hz	1570	Α	
l²t	50 Hz	11 250	A ² s	
	60 Hz	10 230	A-S	
V _{RRM}	Range	400 to 1200	V	
T _J		- 55 to 180	°C	

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS					
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 150 °C mA	
	40	400	500		
80PF(R)(W)	80	800	960	9	
	120	1200	1440		

80PF(R)...(W) Series



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FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current	1	180° conduction, half sine wave		80	Α	
at case temperature	I _{F(AV)}			140	°C	
Maximum RMS forward current	I _{F(RMS)}				126	Α
		t = 10 ms	No voltage		1500	А
Maximum peak, one-cycle forward, non-repetitive surge current	I _{FSM}	t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = 150 ^{\circ}\text{C}$	1570	
		t = 10 ms	100 % V _{RRM} reapplied		1260	
		t = 8.3 ms			1320	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage		11 250	A ² s
		t = 8.3 ms	reapplied		10 230	
		t = 10 ms	100 % V _{RRM}		7950	
		t = 8.3 ms	reapplied		7200	
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		112 500	A²√s	
Low level value of threshold voltage	$V_{F(TO)}$	$(16.7 \% \text{ x } \pi \text{ x } \text{I}_{\text{F(AV)}} < \text{I} < \pi \text{ x } \text{I}_{\text{F(AV)}}), \text{T}_{\text{J}} = \text{T}_{\text{J}} \text{ maximum}$		0.73	V	
Low level value of forward slope resistance	r _f	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum		3.0	mΩ	
Maximum forward voltage drop	V_{FM}	I_{pk} = 220 A, T_J = 25 °C, t_p = 400 μ s rectangular wave 1.40 V		V		

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction operating and storage temperature range	T _J , T _{Stg}		- 55 to 180	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.30	KAM	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.25	K/W	
Maximum allowable mounting torque (+ 0 %, - 10 %)		Not lubricated thread, tighting on nut (1)	3.4 (30)	N⋅m	
		Lubricated thread, tighting on nut (1)	2.3 (20)		
		Not lubricated thread, tighting on hexagon (2)	4.2 (37)	(lbf · in)	
		Lubricated thread, tighting on hexagon (2)	3.2 (28)		
Approximate weight			15.8	g	
			0.56	OZ.	
Case style		See dimensions - link at the end of datasheet DO-203AB (DO-5		AB (DO-5)	

Notes

For technical questions, contact: ind-modules@vishay.com
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⁽¹⁾ Recommended for pass-through holes

⁽²⁾ Torque must be appliable only to hexagon and not to plastic structure, recommended for holed heatsink



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△R _{thJC} CONDUCTION					
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS	
180°	0.14	0.10			
120°	0.16	0.17			
90°	0.21	0.22	$T_J = T_J$ maximum	K/W	
60°	0.30	0.31			
30°	0.50	0.50			

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

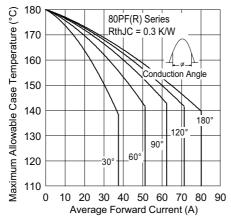


Fig. 1 - Current Ratings Characteristics

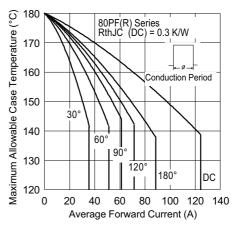


Fig. 2 - Current Ratings Characteristics

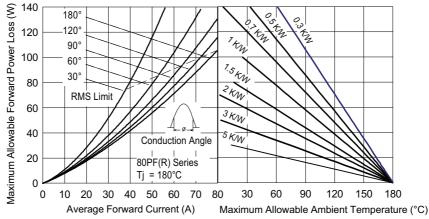


Fig. 3 - Forward Power Loss Characteristics

80PF(R)...(W) Series

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Standard Recovery Diodes, Generation 2 DO-5 (Stud Version), 80 A



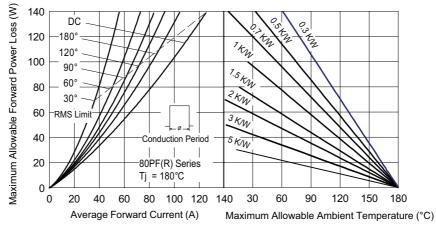
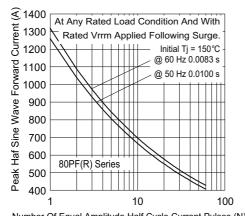


Fig. 4 - Forward Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses (N)
Fig. 5 - Maximum Non-Repetitive Surge Current

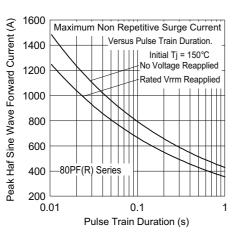


Fig. 6 - Maximum Non-Repetitive Surge Current

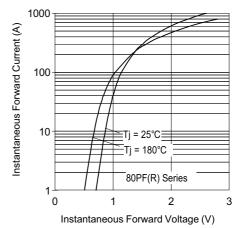


Fig. 7 - Forward Voltage Drop Characteristics

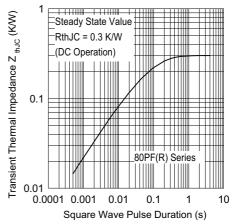
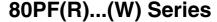


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



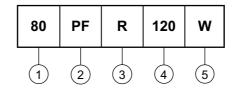


Standard Recovery Diodes, Generation 2 DO-5 (Stud Version), 80 A

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ORDERING INFORMATION TABLE

Device code



- 1 • 80 = Standard device
 - 82 = Isolated lead on standard terminal with silicone sleeve available for 1200 V only (red = Reverse polarity)
 (blue = Normal polarity)
- 2 PF = Plastic package
- None = Stud normal polarity (cathode to stud)
 - R = Stud reverse polarity (anode to stud)
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
 None = Standard terminal
 - (see dimensions for 80PF(R)... link at the end of datasheet)

 W = Wire terminal
 - w wire terminal
 (see dimensions for 80PF(R)...W link at the end of datasheet)

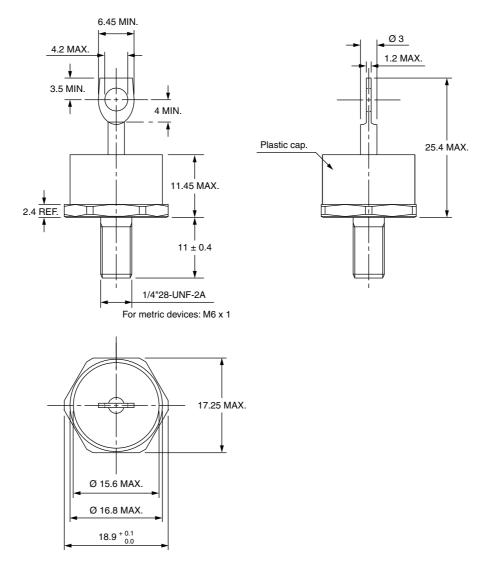
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95345		



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DO-203AB (DO-5) for 50PF(R)...(W), 80PF(R)...(W) and 95PF(R)...(W) Series

DIMENSIONS FOR 80PF(R), 50PF(R) AND 95PF(R) SERIES in millimeters



Note

· For metric device please contact factory

Document Number: 95345 Revision: 26-Aug-08

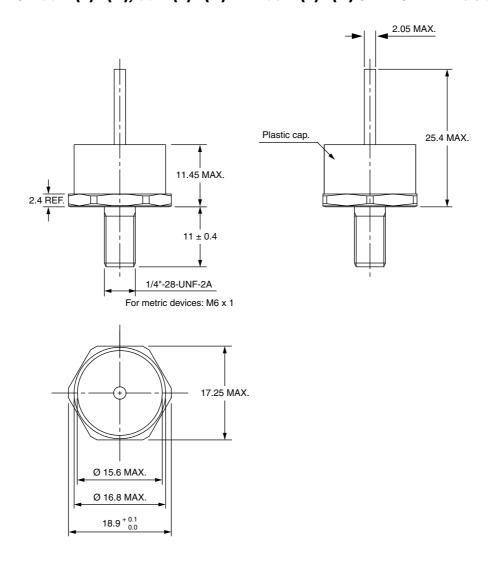
Outline Dimensions

Vishay Semiconductors

DO-203AB (DO-5) for 50PF(R)...(W), 80PF(R)...(W) and 95PF(R)...(W) Series



DIMENSIONS FOR 80PF(R)...(W), 50PF(R)...(W) AND 95PF(R)...(W) SERIES in millimeters



Note

• For metric device please contact factory

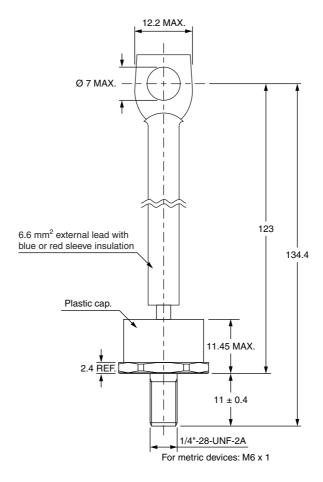




DO-203AB (DO-5) for 50PF(R)...(W), 80PF(R)...(W) and 95PF(R)...(W) Series

Vishay Semiconductors

DIMENSIONS FOR 52PF(R), 82PF(R) AND 97PF(R) SERIES in millimeters



Note

• For metric device please contact factory

Document Number: 95345 Revision: 26-Aug-08

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